

1SS355

Silicon Epitaxial Planar Switching Diode

Features

- Small plastic package suitable
- for surface mounted design
- High reliability with high surge current handling capability

Top View

Marking Code: A Simplified outline SOD-323 and symbol

Applications

• High speed switching

Absolute Maximum Ratings (T_a = 25 °C)

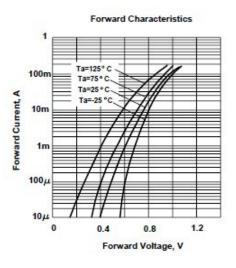
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V _{RM}	90	V
Reverse Voltage	V _R	80	V
Average Rectified Forward Current	I _{F(AV)}	100	mA
Peak Forward Current	I _{FM}	225	mA
Surge Forward Current (1 s)	I _{FSM}	500	mA
Junction Temperature	Tj	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

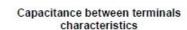
Electrical Characteristics (T_a = 25 °C)

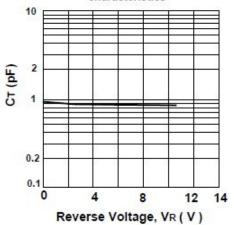
Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 100 mA	V _F	1.2	V
Reverse Current at V _R = 80 V	I _R	0.1	μA
Capacitance between Terminals at V_R = 0.5 V, f = 1 MHz	C _T	3	pF
Reverse Recovery Time at V _R = 6 V, I _F = 10 mA, R _L = 100 Ω	t _{rr}	4	ns



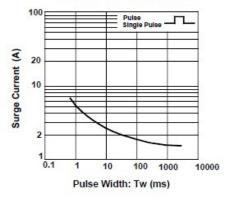
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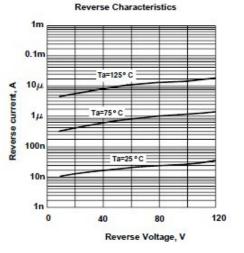




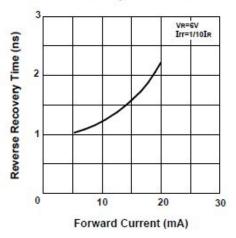


Surge Current Characteristics

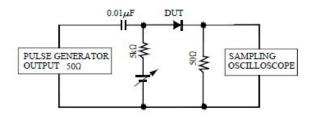




Reverse Recovery Time Characteristics



Reverse Recovery Time Measurement Circuit



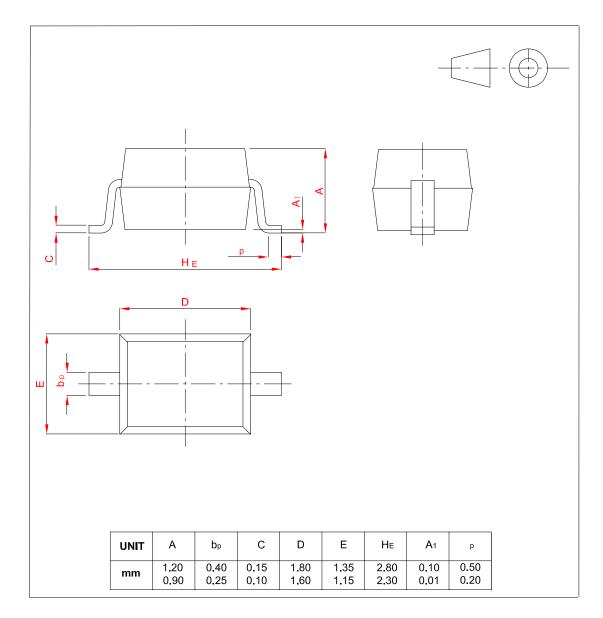


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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



单击下面可查看定价,库存,交付和生命周期等信息

>>SHIKUES(时科)